PROCESS CP392V

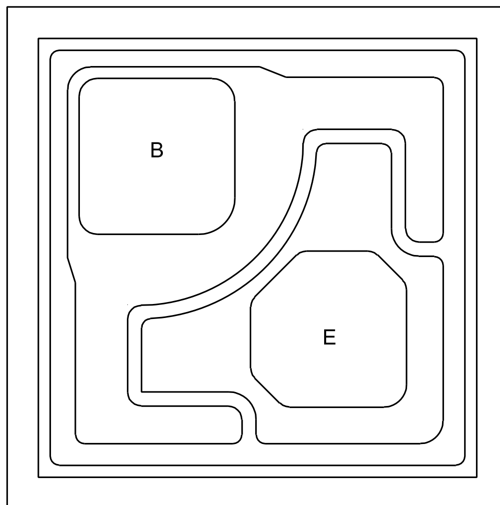
Smal Signal Transistor

NPN - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.7 x 3.7 MILS
Emitter Bonding Pad Area	3.7 x 3.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



R0

BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER
93,826

PRINCIPAL DEVICE TYPES
2N3904
CMKT3904
CMLT3904E
CMPT3904
CMPT3904E
CMST3904
CXT3904
CZT3904

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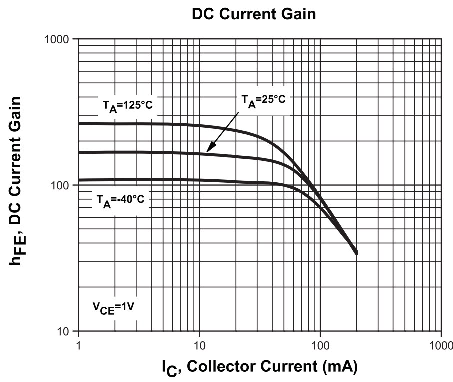
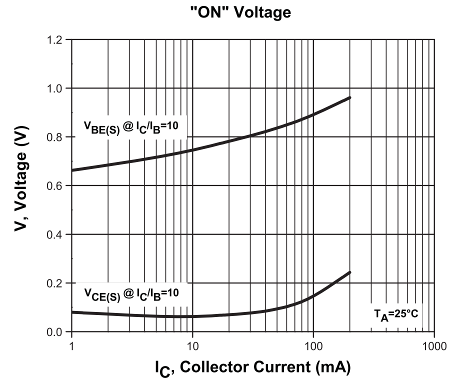
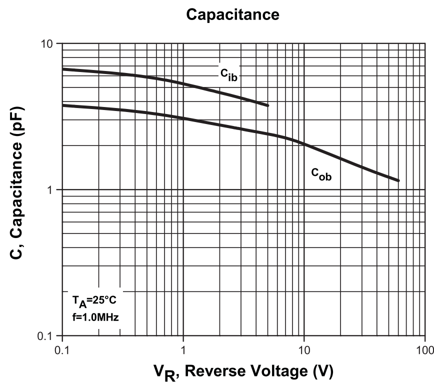
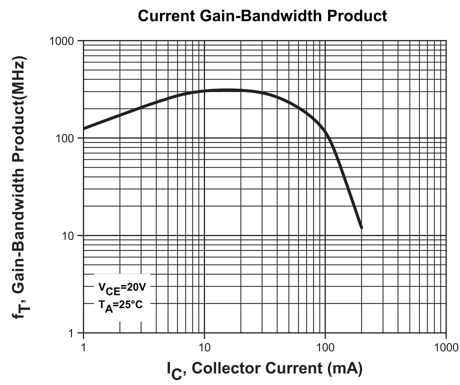
PROCESS CP392V

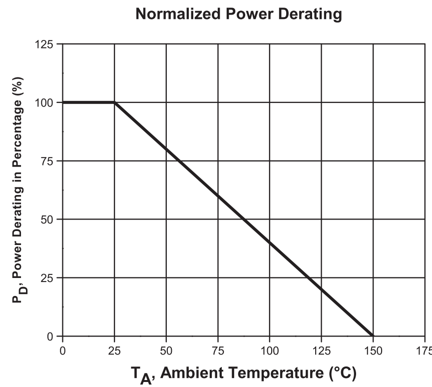
Typical Electrical Characteristics











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